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Mar 29, 1978

DERWENT-ACC-NO: 1978-91060A

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TITLE: Monocrystalline tungsten film deposition for use in electronics - from tungsten hexa:fluoride vapour and hydrogen mixt. on metal backing and vacuum annealing

INVENTOR: KISHMAKHOV, B S L; KOROLEV, Y U M ; NIKOLAEV, Y U V

PATENT-ASSIGNEE:

ASSIGNEE	CODE
KISHMAKOV B SH	KISHI

PRIORITY-DATA: 1973SU-1907188 (April 6, 1973)

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
<input type="checkbox"/> SU 590370 A	March 29, 1978		000	

INT-CL (IPC): C23C 11/02

ABSTRACTED-PUB-NO: SU 590370A

BASIC-ABSTRACT:

The deposition of film or coating is by redn. of tungsten hexafluoride at a backing temp. of 500-800 degrees C at atmos. press. To obtain a monocrystalline coating while retaining high output and the possibility of producing thick coatings the tungsten is deposited on a monocrystalline bcc metal backing and vacuum annealed at 1600-1900 degrees C for 30-60 hrs.

The prod. is used in electronic ind. LN and in thermo electronic transducers.

TITLE-TERMS: MONOCRYSTAL TUNGSTEN FILM DEPOSIT ELECTRONIC TUNGSTEN HEXA FLUORIDE VAPOUR HYDROGEN MIXTURE METAL BACKING VACUUM ANNEAL

DERWENT-CLASS: L03 M13

CPI-CODES: L03-D04A; M13-B;

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